

# Xiang Xiao

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/3548967/publications.pdf>

Version: 2024-02-01

24  
papers

280  
citations

1163117  
8  
h-index

1281871  
11  
g-index

24  
all docs

24  
docs citations

24  
times ranked

518  
citing authors

#	ARTICLE	IF	CITATIONS
1	Photoreactive and Metal-Platable Copolymer Inks for High-Throughput, Room-Temperature Printing of Flexible Metal Electrodes for Thin-Film Electronics. <i>Advanced Materials</i> , 2016, 28, 4926-4934.	21.0	77
2	Low-Voltage a-InGaZnO Thin-Film Transistors With Anodized Thin HfO <sub>2</sub> Gate Dielectric. <i>IEEE Electron Device Letters</i> , 2015, 36, 573-575.	3.9	51
3	Anodized ITO Thin-Film Transistors. <i>Advanced Functional Materials</i> , 2014, 24, 4170-4175.	14.9	41
4	Room-Temperature-Processed Flexible Amorphous InGaZnO Thin Film Transistor. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 25850-25857.	8.0	36
5	A Back-Channel-Etched Amorphous InGaZnO Thin-Film Transistor Technology With Al-Doped ZnO as Source/Drain and Pixel Electrodes. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 2205-2209.	3.0	15
6	Indium-Tin-Oxide Thin-Film Transistors With In Situ Anodized Ta <sub>2</sub> O <sub>5</sub> Passivation Layer. <i>IEEE Electron Device Letters</i> , 2016, 37, 603-606.	3.9	12
7	a-IGZO TFTs With Inductively Coupled Plasma Chemical Vapor Deposited $\text{SiO}_x$ Gate Dielectric. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 2687-2690.	3.0	10
8	Back Channel Anodization Amorphous Indium Gallium Zinc Oxide Thin-Film Transistors Process. <i>IEEE Electron Device Letters</i> , 2015, 36, 357-359.	3.9	9
9	Fabrication of p-type copper oxide thin-film transistors at different oxygen partial pressure. , 2014, , .		6
10	P <sub>9</sub> : Improved Electrical Stability of Double-Gate a-IGZO TFTs. <i>Digest of Technical Papers SID International Symposium</i> , 2015, 46, 1151-1154.	0.3	5
11	A Multi- $V_{th}$ a-IGZO TFT Technology Using Anodization to Selectively Reduce Oxygen Vacancy Concentration in Channel Regions. <i>IEEE Electron Device Letters</i> , 2014, 35, 1248-1250.	3.9	3
12	Comparative study of a-IGZO TFTs with direct current and radio frequency sputtered channel layers. <i>Journal of the Society for Information Display</i> , 2015, 23, 306-312.	2.1	3
13	Estimation of threshold voltage shift in a-IGZO TFTs under different bias temperature stress by improved stretched-exponential equation. , 2016, , .		3
14	Characteristics of double-gate a-IGZO TFT. , 2014, , .		2
15	Effects of over-etching time on the characteristics of amorphous IGZO thin-film transistors with back-channel-etch structure. , 2015, , .		2
16	Indium gallium zinc oxide - Carbon nanotube composite thin film transistor. , 2014, , .		1
17	Study on the transition between p and n types of SnO <sub>x</sub> film deposited by DC sputtering. , 2014, , .		1
18	Impacts of substrate heating schemes on characteristics of amorphous indium-gallium-zinc-oxide (a-IGZO) TFTs fabricated on flexible substrates. , 2014, , .		1

#	ARTICLE	IF	CITATIONS
19	Comparison of N <sub>2</sub> and Ar plasma treatment for source/drain formation in self-aligned top-gate amorphous InGaZnO thin film transistor. , 2016, , .		1
20	Oxygen partial pressure and annealing temperature influence on the performance of back-channel-etch zinc tin oxide thin film transistors. , 2016, , .		1
21	Homojunction In <sub>2</sub> O <sub>3</sub> -TFTs prepared by anodization technique. , 2014, , .		0
22	Fabrication of indium-tin-oxide thin-film transistor using anodization. , 2014, , .		0
23	Impact of wet etchant with different PH value on the performance of back-channel-etch a-IGZO thin-film-transistor. , 2016, , .		0
24	Characteristics of amorphous In-Ga-Zn-O thin-film-transistors with channel layer deposited by bias sputtering. , 2016, , .		0